



**最大额定值**
**Absolute Maximum Ratings**

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	数值 Value	单位 Unit
$V_{CES}$	集电极-发射极电压 Collector-emitter voltage	$V_{GE} = 0V, T_C = 25\text{ }^\circ\text{C}$	750	V
$V_{GES}$	栅极-发射极电压 Gate-emitter voltage	$T_C = 25\text{ }^\circ\text{C}$	$\pm 20$	V
$I_C$	集电极电流 Collector-emitter current	$T_F = 75\text{ }^\circ\text{C}, T_{vj\text{ max}} = 175\text{ }^\circ\text{C}$	550	A
$I_{C(PK)}$	集电极峰值电流 Peak collector current	$t_p = 1\text{ ms}$	1600	A
$P_{max}$	晶体管部分最大损耗 Max. transistor power dissipation	$T_F = 25\text{ }^\circ\text{C}, T_{vj\text{ max}} = 175\text{ }^\circ\text{C}$	1744	W
$I_{t}$	二极管 $I_{t}$ 值 Diode $I_{t}$	$V_R = 0V, t_p = 10\text{ ms}, T_{vj} = 150\text{ }^\circ\text{C}$	TBD	$\text{kA}^2\text{s}$
$V_{isol}$	绝缘电压(模块) Isolation voltage – per module	短接所有端子, 端子与基板间施加电压 (Commoned terminals to base plate), AC RMS, 1 min, 50Hz, $T_C = 25\text{ }^\circ\text{C}$	2500	V

**热和机械数据**
**Thermal & Mechanical Data**

参数 Symbol	说明 Explanation	值 Value	单位 Unit
爬电距离 Creepage distance	端子-散热器 Terminal to heatsink	7.0	mm
	端子-端子 Terminal to terminal	5.5	mm
绝缘间隙 Clearance	端子-散热器 Terminal to heatsink	7.0	mm
	端子-端子 Terminal to terminal	5.0	mm
相对漏电起痕指数 CTI (Comparative Tracking Index)		>200	

**热和机械数据**
**Thermal & Mechanical Data**

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	最小值 Min.	最大值 Max.	单位 Unit
$R_{th(J-F) IGBT}$	IGBT 热阻 Thermal resistance – IGBT	冷却液: 100%水; $\Delta V/\Delta t=10 \text{ dm}^3/\text{min}$ Cooling Fluid: 100% Water; $\Delta V/\Delta t=10 \text{ dm}^3/\text{min}$		86	K / kW
$R_{th(J-F) Diode}$	二极管热阻 Thermal resistance – Diode			128	K / kW
$T_{vj op}$	工作结温 Operating junction temperature	IGBT 部分 ( IGBT )	-40	150	°C
		二极管部分 ( Diode )	-40	150	°C
$T_{stg}$	存储温度 Storage temperature range		-40	125	°C
$M$	安装力矩 Screw torque	安装紧固用 – M6 Module Mounting – M6	3	6	Nm
		电路互连用 – M6 Electrical connections – M6	2.5	5	Nm

**热敏电阻数据**
**NTC-Thermistor Data**

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
$R_{25}$	额定电阻值 Rated resistance	$T_C = 25 \text{ }^\circ\text{C}$		5		kΩ
$\Delta R/R$	R 100 偏差 Deviation of R100	$T_C = 100 \text{ }^\circ\text{C}, R_{100}=493\Omega$	-5		5	%
$P_{25}$	耗散功率 Power dissipation	$T_C = 25 \text{ }^\circ\text{C}$			20	mW
$B_{25/50}$	B -值 B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298.15 \text{ K}))]$		3375		K
$B_{25/80}$	B -值 B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298.15 \text{ K}))]$		3411		K
$B_{25/100}$	B -值 B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298.15 \text{ K}))]$		3433		K

**电特性值**
**Electrical Characteristics**

 除非特别声明，否则  $T_C = 25\text{ }^\circ\text{C}$ 
 $T_C = 25\text{ }^\circ\text{C}$  unless otherwise stated

符号 Symbol	参数名称 Parameter	条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
$I_{CES}$	集电极截止电流 Collector cut-off current	$V_{GE} = 0V, V_{CE} = V_{CES}$			1	mA
		$V_{GE} = 0V, V_{CE} = V_{CES}, T_{vj} = 125\text{ }^\circ\text{C}$			20	mA
		$V_{GE} = 0V, V_{CE} = V_{CES}, T_{vj} = 150\text{ }^\circ\text{C}$			30	mA
$I_{GES}$	栅极漏电流 Gate leakage current	$V_{GE} = \pm 20V, V_{CE} = 0V$			0.5	$\mu\text{A}$
$V_{GE(TH)}$	栅极-发射极阈值电压 Gate threshold voltage	$I_C = 20\text{mA}, V_{GE} = V_{CE}$	5.1	5.9	6.6	V
$V_{CE(sat)}^{(*1)}$	集电极-发射极饱和电压 Collector-emitter saturation voltage	$V_{GE} = 15V, I_C = 550A$		1.45	1.85	V
		$V_{GE} = 15V, I_C = 550A, T_{vj} = 125\text{ }^\circ\text{C}$		1.60	2.00	V
		$V_{GE} = 15V, I_C = 550A, T_{vj} = 150\text{ }^\circ\text{C}$		1.65	2.05	V
$I_F$	二极管正向直流电流 Diode forward current	DC		550		A
$I_{FRM}$	二极管正向重复峰值电流 Diode peak forward current	$t_p = 1\text{ms}$		1600		A
$V_F^{(*1)}$	二极管正向电压 Diode forward voltage	$I_F = 550A, V_{GE} = 0$		1.45	1.85	V
		$I_F = 550A, V_{GE} = 0, T_{vj} = 125\text{ }^\circ\text{C}$		1.50	1.90	V
		$I_F = 550A, V_{GE} = 0, T_{vj} = 150\text{ }^\circ\text{C}$		1.50	1.90	V
$I_{SC}$	短路电流 Short circuit current	$T_{vj} = 150\text{ }^\circ\text{C}, V_{CC} = 300V,$ $V_{GE} \leq 15V, t_p \leq 6\mu\text{s},$ $V_{CE(max)} = V_{CES} - L^{(*2)} \times di/dt,$ IEC 6074-9		3200		A

**注意:** 1.(\*1) 表示该参数的测试点为辅助母排端子 (\*1) indicates it is measured at the auxiliary busbar terminal),

**Note:** 2.(\*2) 表示  $L$  是电路杂散电感加上  $L_M$  (\*2) indicates  $L$  is the circuit stray inductance plus  $L_M$ ).

**电特性值**
**Electrical Characteristics**

 除非特别声明，否则  $T_C = 25\text{ }^\circ\text{C}$ 
 $T_C = 25\text{ }^\circ\text{C}$  unless otherwise stated

符号 Symbol	参数名称 Parameter	条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
$C_{ies}$	输入电容 Input capacitance	$V_{CE} = 25V, V_{GE} = 0V, f = 100kHz$		46		nF
$Q_g$	栅极电荷 Gate charge	$\pm 15V$		5.7		$\mu C$
$C_{res}$	反向传输电容 Reverse transfer capacitance	$V_{CE} = 25V, V_{GE} = 0V, f = 100kHz$		1.6		nF
$L_M$	模块电感 Module inductance			14		nH
$R_{INT}$	内阻 Internal transistor resistance			0.75		m $\Omega$

**电特性值**
**Electrical Characteristics**

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit	
$t_{d(off)}$	关断延迟时间 Turn-off delay time	$I_C = 550A,$ $V_{CE} = 300V,$ $V_{GE} = \pm 15V,$ $R_{G(OFF)} = 1.0\Omega,$ $L_S = 40nH,$ $dv/dt = 2600V/us$	$T_{vj} = 25\text{ }^\circ\text{C}$	660		ns	
			$T_{vj} = 125\text{ }^\circ\text{C}$	690			
			$T_{vj} = 150\text{ }^\circ\text{C}$	720			
$t_f$	下降时间 Fall time		$T_{vj} = 25\text{ }^\circ\text{C}$		76		ns
			$T_{vj} = 125\text{ }^\circ\text{C}$		190		
			$T_{vj} = 150\text{ }^\circ\text{C}$		225		
$E_{OFF}$	关断损耗 Turn-off energy loss		$T_{vj} = 25\text{ }^\circ\text{C}$		35		mJ
			$T_{vj} = 125\text{ }^\circ\text{C}$		40		
			$T_{vj} = 150\text{ }^\circ\text{C}$		41		
$t_{d(on)}$	开通延迟时间 Turn-on delay time	$I_C = 550A,$ $V_{CE} = 300V,$ $V_{GE} = \pm 15V,$ $R_{G(ON)} = 1.0\Omega,$ $L_S = 40nH,$ $di/dt = 5000A/us$	$T_{vj} = 25\text{ }^\circ\text{C}$		192	ns	
			$T_{vj} = 125\text{ }^\circ\text{C}$		186		
			$T_{vj} = 150\text{ }^\circ\text{C}$		180		
$t_r$	上升时间 Rise time		$T_{vj} = 25\text{ }^\circ\text{C}$		106		ns
			$T_{vj} = 125\text{ }^\circ\text{C}$		114		
			$T_{vj} = 150\text{ }^\circ\text{C}$		115		
$E_{ON}$	开通损耗 Turn-on energy loss		$T_{vj} = 25\text{ }^\circ\text{C}$		7.2		mJ
			$T_{vj} = 125\text{ }^\circ\text{C}$		8.2		
			$T_{vj} = 150\text{ }^\circ\text{C}$		8.8		
$Q_{rr}$	二极管反向恢复电荷 Diode reverse recovery charge	$T_{vj} = 25\text{ }^\circ\text{C}$		44		$\mu\text{C}$	
		$T_{vj} = 125\text{ }^\circ\text{C}$		68			
		$T_{vj} = 150\text{ }^\circ\text{C}$		83			
$I_{rr}$	二极管反向恢复电流 Diode reverse recovery current	$T_{vj} = 25\text{ }^\circ\text{C}$		295		A	
		$T_{vj} = 125\text{ }^\circ\text{C}$		330			
		$T_{vj} = 150\text{ }^\circ\text{C}$		350			
$E_{rec}$	二极管反向恢复损耗 Diode reverse recovery energy	$T_{vj} = 25\text{ }^\circ\text{C}$		13		mJ	
		$T_{vj} = 125\text{ }^\circ\text{C}$		20			
		$T_{vj} = 150\text{ }^\circ\text{C}$		24			

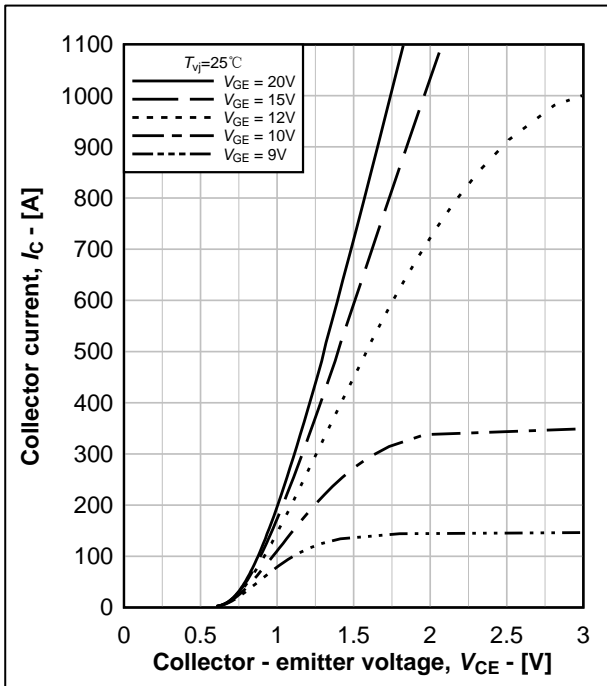


图 3. IGBT 输出特性典型曲线,  $I_C = f(V_{CE})$

Fig.3 Typical IGBT output characteristics,  $I_C = f(V_{CE})$

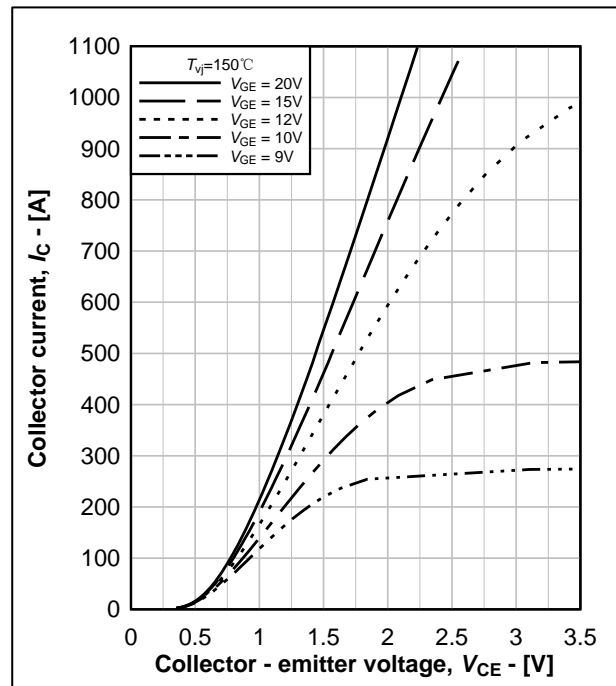


图 4. IGBT 输出特性典型曲线,  $I_C = f(V_{CE})$

Fig.4 Typical IGBT output characteristics,  $I_C = f(V_{CE})$

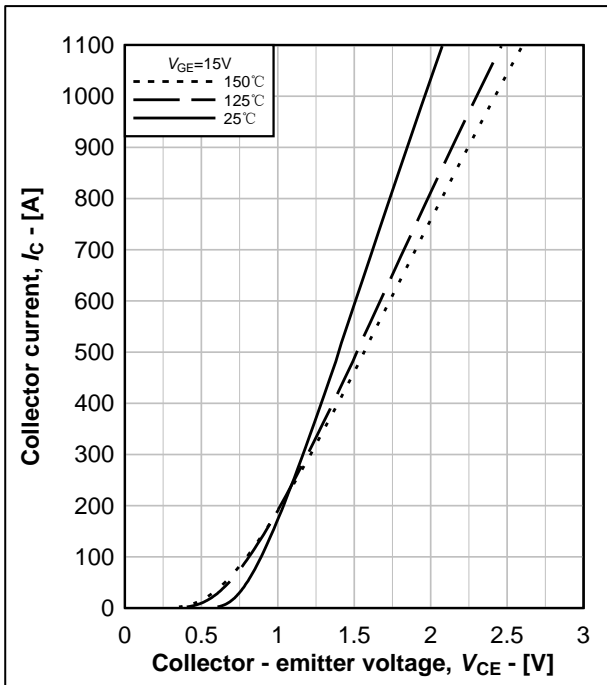


图 5. IGBT 输出特性典型曲线,  $I_C = f(V_{CE})$

Fig.5 Typical IGBT output characteristics,  $I_C = f(V_{CE})$

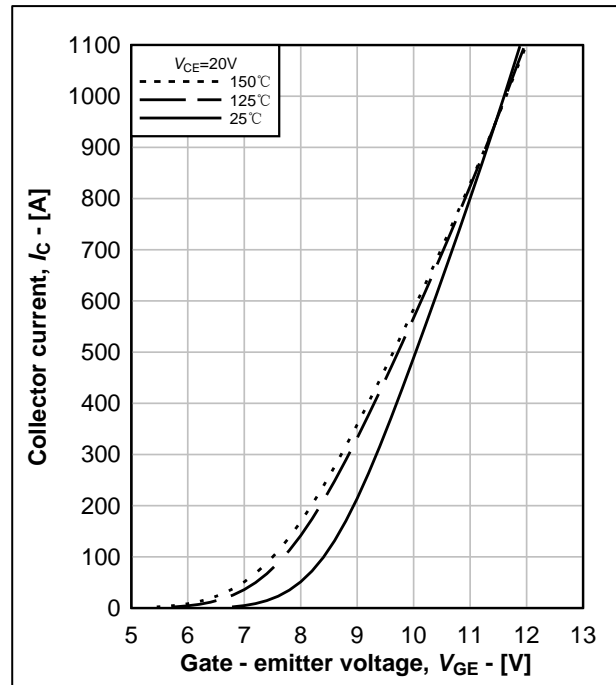


图 6. IGBT 传输特性典型曲线,  $I_C = f(V_{GE})$

Fig.6 Typical IGBT transfer characteristics,  $I_C = f(V_{GE})$

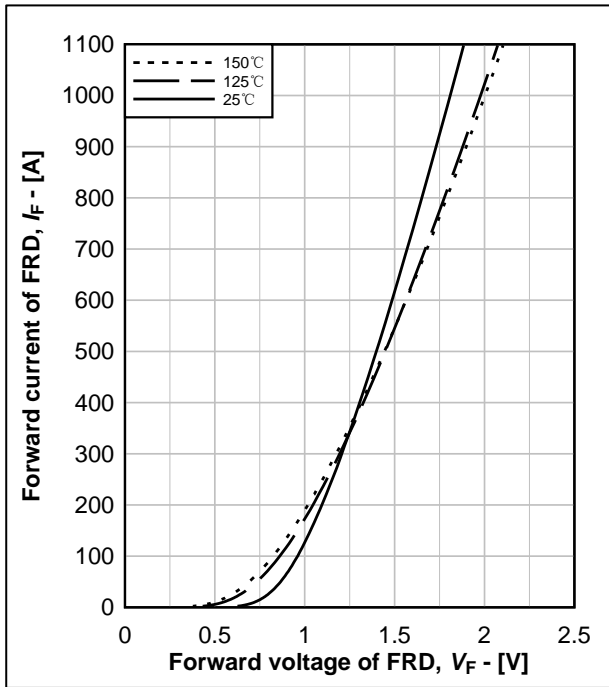


图 7. FRD 输出特性典型曲线,  $I_F = f(V_F)$

Fig.7 Typical FRD output characteristics,  $I_F = f(V_F)$

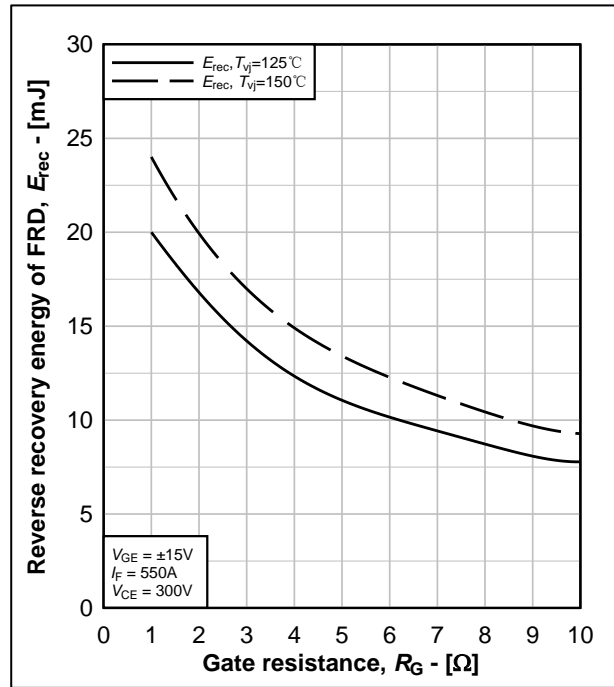


图 8. FRD 反向恢复能耗典型曲线,  $E_{rec} = f(R_G)$

Fig.8 Typical FRD  $E_{rec}$ ,  $E_{rec} = f(R_G)$

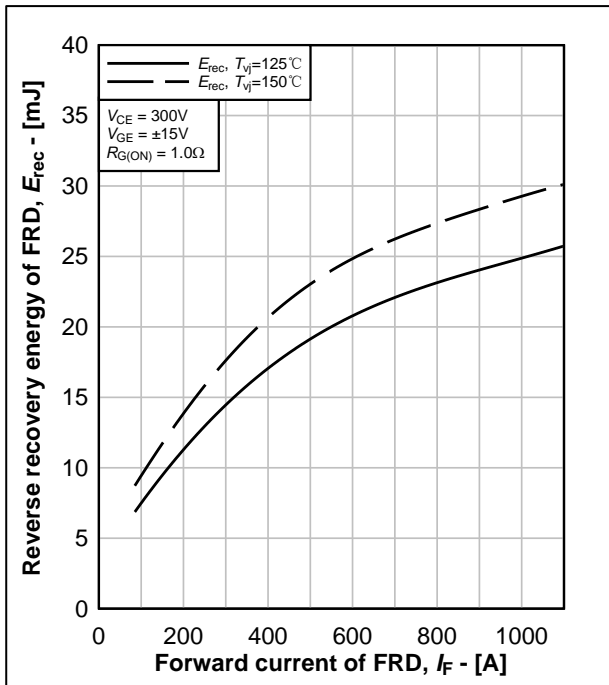


图 9. FRD 反向恢复能耗典型曲线,  $E_{rec} = f(I_F)$

Fig.9 Typical FRD  $E_{rec}$ ,  $E_{rec} = f(I_F)$

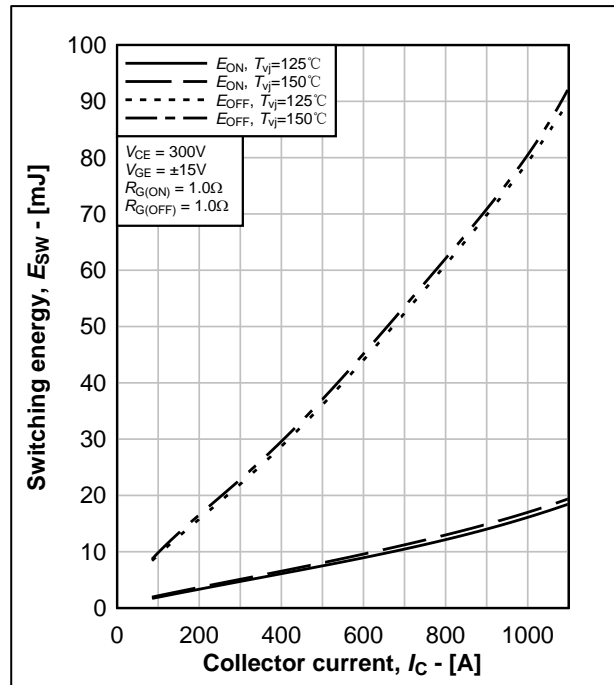


图 10. IGBT 开关能耗典型曲线,  $E_{ON} = f(I_c)$ ,  $E_{OFF} = f(I_c)$

Fig.10 Typical IGBT switching energy,

$E_{ON} = f(I_c)$ ,  $E_{OFF} = f(I_c)$



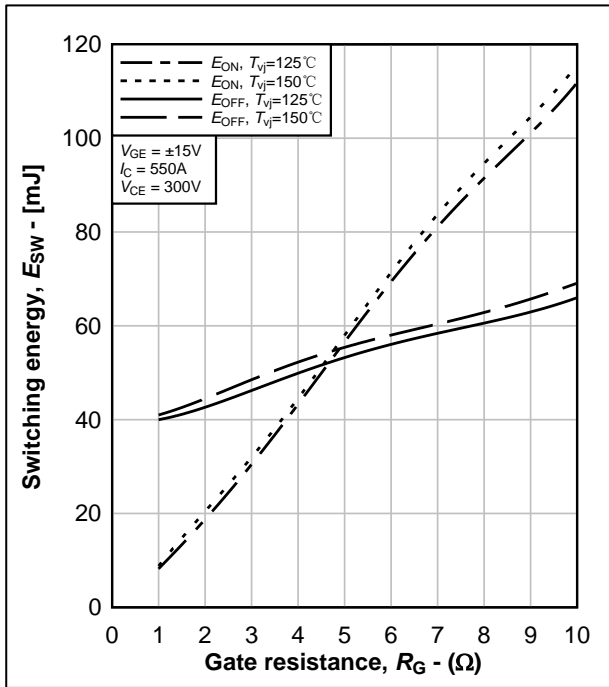

 图 11. IGBT 开关能耗典型曲线,  $E_{ON} = f(R_G)$ ,  $E_{OFF} = f(R_G)$ 

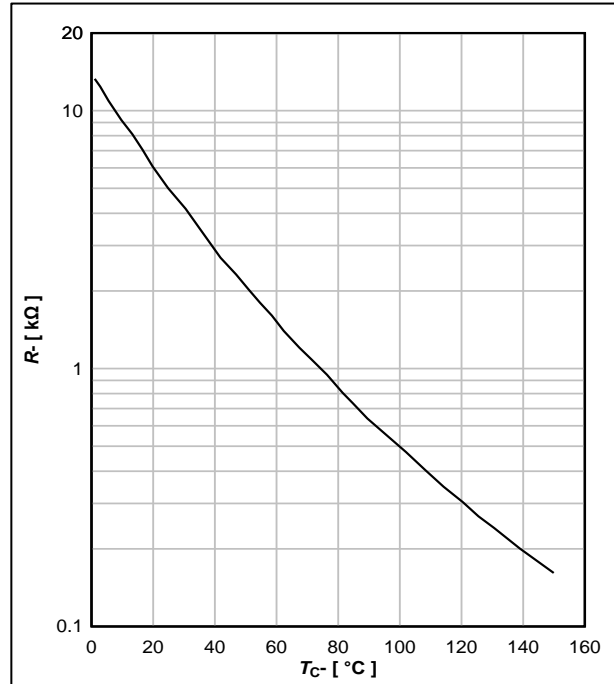
 Fig.11 Typical IGBT switching energy,  
 $E_{ON} = f(R_G)$ ,  $E_{OFF} = f(R_G)$ 

 图 12. 热敏电阻典型特性曲线,  $R = f(T_C)$ 

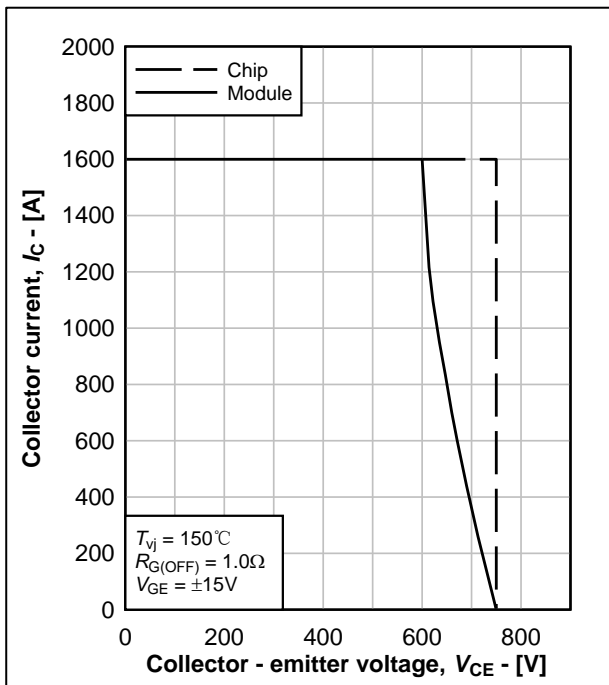
 Fig.12 Typical NTC thermistor characteristic,  $R = f(T_C)$ 

 图 13. IGBT 反偏安全工作区,  $I_C = f(V_{CE})$ 

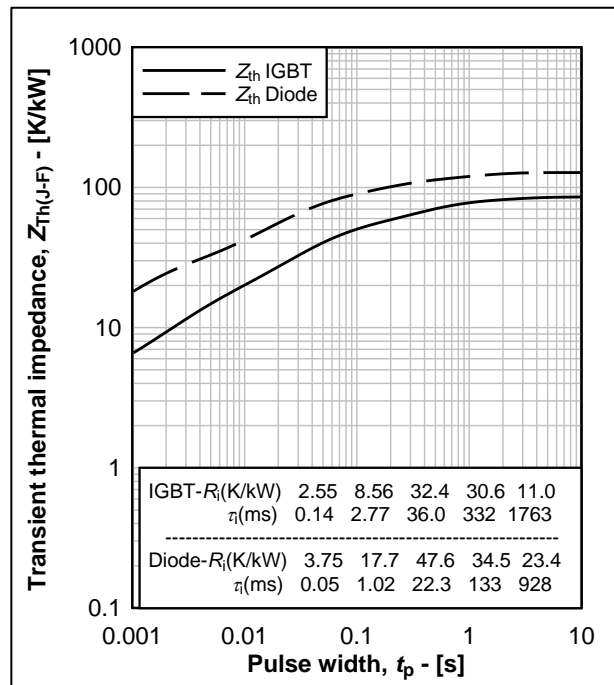
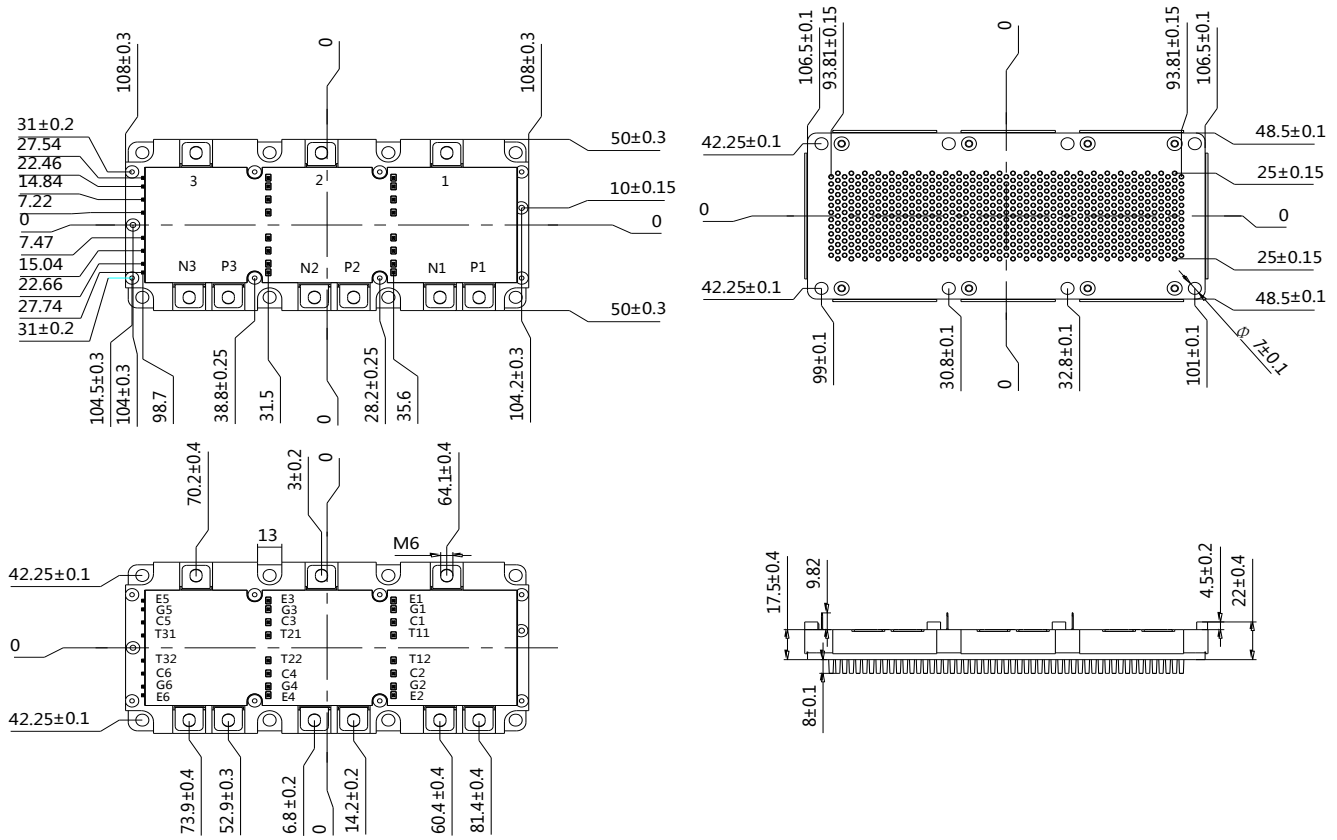
 Fig.13 Reverse bias safe operating area of IGBT,  
 $I_C = f(V_{CE})$ 

 图 14. 瞬态热阻抗曲线,  $Z_{Th(J-F)} = f(t_p)$ 

 Fig.14 Transient thermal impedance,  $Z_{Th(J-F)} = f(t_p)$



重量 Weight: 1300g

模块外观类型 Module outline code: S1

图 15. 模块外观尺寸

Fig. 15 Module outlines

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